

IN THE CLAIMS

Please amend the claims as follows:

Claim 1. (currently amended) A method of fabricating a semiconductor wafer, comprising:

- (a) disposing a volume of an aqueous slurry containing an abrasive material onto a semiconductor wafer and polishing a the semiconductor wafer with a polishing pad; and
- (b) disposing a volume of a nonaqueous solvent onto said semiconductor wafer.

Claim 2 (canceled).

Claim 3 (original). The method of claim 1, wherein:

said polishing pad is in contact with said semiconductor wafer when said nonaqueous solvent is disposed onto said semiconductor wafer.

Claim 4 (canceled).

Claim 5 (currently amended). The method of claim 21 4, further comprising wherein:

~~(e) includes~~ increasing the weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous

Claim 6 (original). The method of claim 5, wherein:

said weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous solvent mixture is increased until said aqueous slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

Claim 7 (original). The method of claim 1, wherein:

said nonaqueous solvent includes an ammine.

Claim 8 (original). The method of claim 1, wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 9 (previously presented). The method of claim 1, wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 10 (original). The method of claim 1, wherein:

said nonaqueous solvent includes analine.

Claim 11 (original). The method of claim 1, wherein:

said nonaqueous solvent includes N,N-dimethylaniline.

Claim 12 (currently amended). A method of fabricating a semiconductor wafer, comprising:

(a) subjecting a front side of said semiconductor wafer to chemical mechanical polishing using an aqueous slurry; and

(b) disposing a volume of a nonaqueous solvent onto said front side of said semiconductor wafer during said chemical mechanical polishing.

Claim 13 (original). The method of claim 12, wherein:

said nonaqueous solvent includes an ammine.

Claim 14 (original). The method of claim 12, wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 15 (previously presented). The method of claim 12, wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 16 (original). The method of claim 12, wherein:

said nonaqueous solvent includes analine.

Claim 17 (original). The method of claim 12, wherein:

said nonaqueous solvent includes N,N-dimethylaniline.

Claims 18-20 (canceled).

Claim 21. (new) A method of fabricating a semiconductor wafer, comprising:

(a) mixing an aqueous slurry containing an abrasive material and a nonaqueous solvent in a mixing unit so as to create an aqueous slurry/nonaqueous solvent mixture prior to being disposed onto said semiconductor wafer;

(b) disposing a volume of the aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto a semiconductor wafer; and

(c) polishing the semiconductor wafer with a polishing pad.